FEATURES

- Side-looking plastic package
- 55° (nominal) acceptance angle
- Wide sensitivity ranges
- TTL/LSTTL/CMOS compatible
- Buffer (SDP8600/8601/8602) or inverting (SDP8610/8611/8612) logic available
- Three different lead spacing arrangements

The SDP86XX series is a family of single chip

Optoschmitt IC detectors molded in a side-looking black

plastic package to minimize the effect of visible ambient light. The photodetector consists of a photodiode, amplifier, voltage regulator, Schmitt trigger and an NPN

output transistor with a 10 k Ω (nominal) pull-up resistor.

Output rise and fall times are independent of the rate of

internally temperature compensated. Flexibility of use is

in.(1.27 mm) offset pin circle (SDP8600/8610) and 0.10

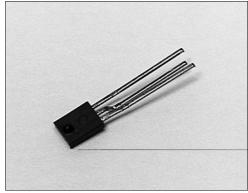
change of incident light. Detector sensitivity has been

enhanced by a choice of three different lead

configurations; in-line (SDP8601/8611), 0.05

in. (2.54 mm) offset center lead (SDP8602/8612).

 Mechanically and spectrally matched to SEP8506 and SEP8706 infrared emitting diodes

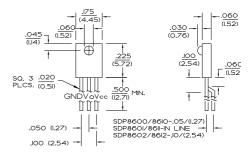


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OUTLINE DIMENSIONS in inches (mm)

Tolerance	3 plc decimals			
	2 plc decimals			

 $\pm 0.005(0.12)$ $\pm 0.020(0.51)$



Device Polarity:

DESCRIPTION

- Buffer Output is HI when incident light intensity is above the turn- on threshold level.
- Inverter Output is LO when incident light intensity is above the turn- on threshold level.

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Honeywell reserves the right to make changes in order to improve design and supply the best products possible.

ELECTRICAL CHARACTERISTICS (-40°C to +85°C unless otherwise noted)

PARAMETER	SYMBOL	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Operating Supply Voltage	Vcc	4.5		12.0	V	T _A =25°C
Turn-on Threshold Irradiance SDP86XX-001 SDP86XX-002 SDP86XX-003	Eet(+)			2.5 1.2 0.6	mW/cm ²	Vcc=5 V T _A =25°C (2)
Hysteresis ⁽³⁾	HYST	5		30	%	
Supply Current	lcc			12.0 15.0	mA	Ee=0 Or 3.0 mW/cm² Vcc=5 V Vcc=12 V
High Level Output Voltage SDP8600/8601/8602 SDP8610/8611/8612	Vон	2.4 2.4			V	Vcc=5 V, Iон=0 Ee=3.0 mW/cm² Ee=0
Low Level Output Voltage SDP8600/8601/8602 SDP8610/8611/8612	Vol			0.4 0.4	V	V _{CC} =5 V, I _{OL} =12.8 mA Ee=0 Ee=3.0 mW/cm²
Internal Pull-Up Resistor	RINT	5.0	10.0	20.0	kΩ	
Operate Point Temperature Coefficient	Ортс		-0.76		%/°C	Emitter @ Constant Temperature
Output Rise Time	tr		60		ns	R∟=390 Ω, C∟=50 pF
Output Fall Time	t _f		15		ns	RL=390 Ω, CL=50 pF
Propagation Delay, Low-High, High-Low	t _{PLH} , t _{PHL}		5.0		μs	R∟=390 Ω, C∟=50 pF
Clock Frequency				100	kHz	RL=390 Ω, CL=50 pF

Notes

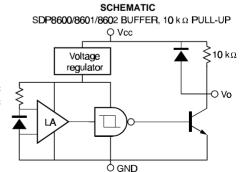
1. It is recommended that a bypass capacitor, 0.1 μF typical, be added between V_{CC} and GND near the device in order to stabilize power supply line.

2. The radiation source is an IRED with a peak wavelength of 935 nm.

3. Hysteresis is defined as the difference between the operating and release threshold intensities, expressed as a percentage of the operate threshold intensity.

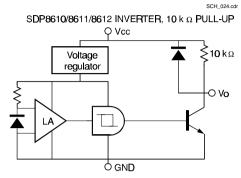
ABSOLUTE MAXIMUM RATINGS

Supply Voltage	12 V (1)
Duration of Output	
Short to V _{cc} or Ground	1.0 sec
Output Current	18 mA
Operating Temperature Range	-40°C to 85°C
Storage Temperature Range	-40°C to 85°C
Soldering Temperature (5 sec)	240°C
Notes 1. Derate linearly from 25° C to 5.5 V at 85° C.	





SCHEMATIC



SWITCHING WAVEFORM FOR BUFFERS

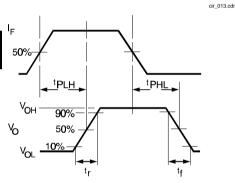
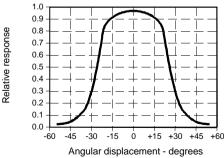
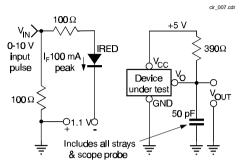


Fig. 1 Responsivity vs Angular Displacement



SWITCHING TIME TEST CIRCUIT



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SWITCHING WAVEFORM FOR INVERTERS

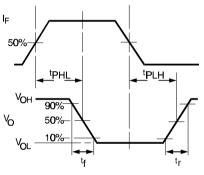
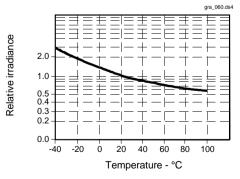
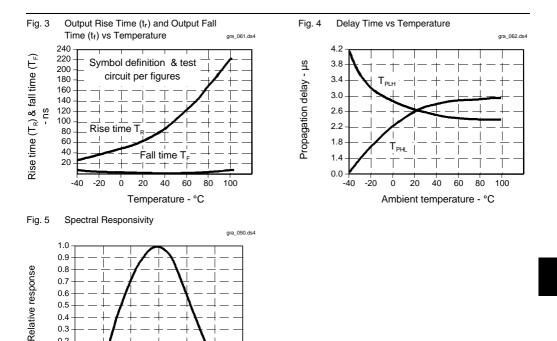


Fig. 2 Threshold Irradiance vs Temperature



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0.4 0.3 0.2 0.1 0.0

600

700

900

Wavelength - nm

1000 1100 1200

800

All Performance Curves Show Typical Values

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